

# MMD60R750P

## 600V 0.75Ω N-channel MOSFET

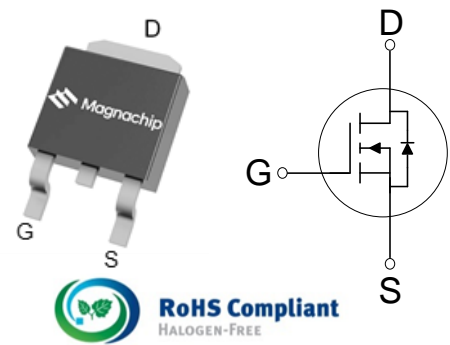
### ■ Description

MMD60R750P is power MOSFET using Magnachip's advanced super junction technology that can realize very low on-resistance and gate charge. It will provide much high efficiency by using optimized charge coupling technology. These user friendly devices give an advantage of Low EMI to designers as well as low switching loss.

### ■ Key Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max}$	0.75	Ω
$V_{TH,typ}$	3	V
$I_D$	5.7	A
$Q_{g,typ}$	15	nC

### ■ Package & Internal Circuit



### ■ Features

- Low Power Loss by High Speed Switching and Low On-Resistance
- 100% Avalanche Tested
- Green Package – Pb Free Plating, Halogen Free

### ■ Applications

- PFC Power Supply Stages
- Switching Applications
- Adapter
- Motor Control
- DC – DC Converters

### ■ Ordering Information

Order Code	Marking	Temp. Range	Package	Packing	RoHS Status
MMD60R750PRH	60R750P	-55 ~ 150 °C	TO-252	Reel & Tape	Halogen Free

■ Absolute Maximum Rating ( $T_c=25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Rating	Unit	Note
Drain – Source voltage	$V_{DSS}$	600	V	
Gate – Source voltage	$V_{GSS}$	$\pm 30$	V	
Continuous drain current	$I_D$	5.7	A	$T_c=25^\circ\text{C}$
		3.6	A	$T_c=100^\circ\text{C}$
Pulsed drain current <sup>(1)</sup>	$I_{DM}$	17.1	A	
Power dissipation	$P_D$	48	W	
Single - pulse avalanche energy	$E_{AS}$	75	mJ	
MOSFET dv/dt ruggedness	dv/dt	50	V/ns	
Diode dv/dt ruggedness	dv/dt	15	V/ns	
Storage temperature	$T_{stg}$	-55 ~150	$^\circ\text{C}$	
Maximum operating junction temperature	$T_j$	150	$^\circ\text{C}$	

1) Pulse width  $t_P$  limited by  $T_{j,max}$

2)  $I_{SD} \leq I_D$ ,  $V_{DS\ peak} \leq V_{(BR)DSS}$

■ Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case max	$R_{thjc}$	2.6	$^\circ\text{C/W}$
Thermal resistance, junction-ambient max	$R_{thja}$	62.5	$^\circ\text{C/W}$

**■ Static Characteristics ( $T_c=25^\circ\text{C}$  unless otherwise specified)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Drain – Source Breakdown voltage	$V_{(BR)DSS}$	600	-	-	V	$V_{GS} = 0V, I_D=0.25mA$
Gate Threshold Voltage	$V_{GS(th)}$	2	3	4	V	$V_{DS} = V_{GS}, I_D=0.25mA$
Zero Gate Voltage Drain Current	$I_{DSS}$	-	-	1	$\mu A$	$V_{DS} = 600V, V_{GS} = 0V$
Gate Leakage Current	$I_{GSS}$	-	-	100	nA	$V_{GS} = \pm 30V, V_{DS} = 0V$
Drain-Source On State Resistance	$R_{DS(ON)}$	-	0.68	0.75	$\Omega$	$V_{GS} = 10V, I_D = 2.0A$

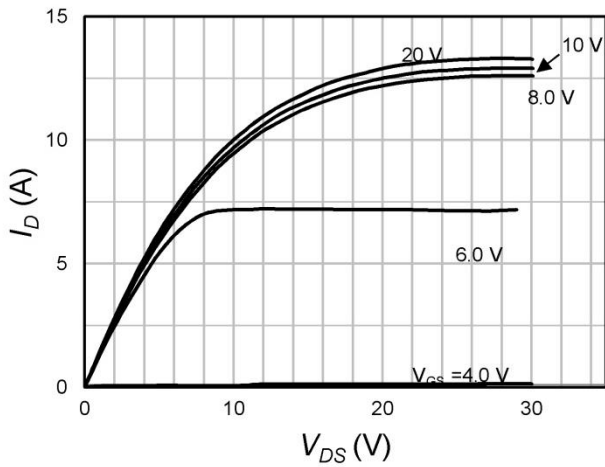
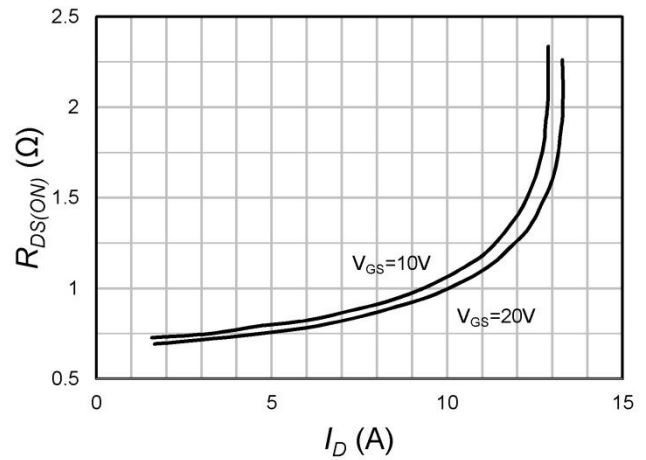
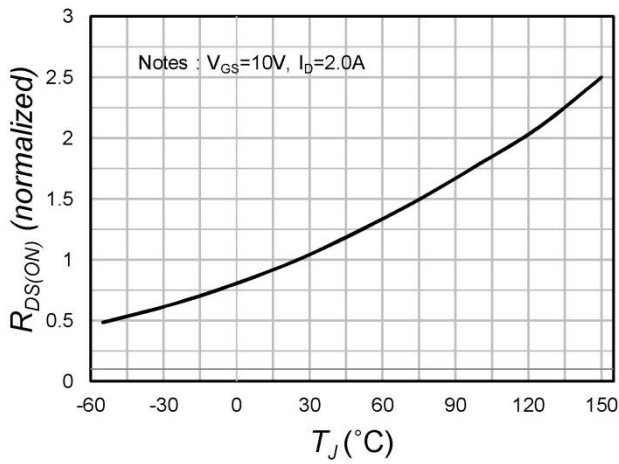
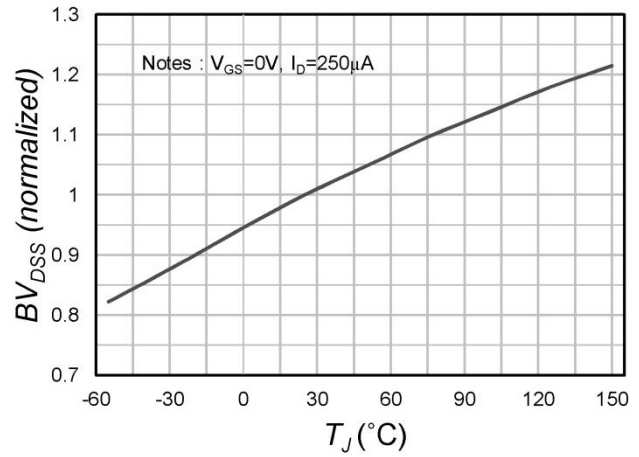
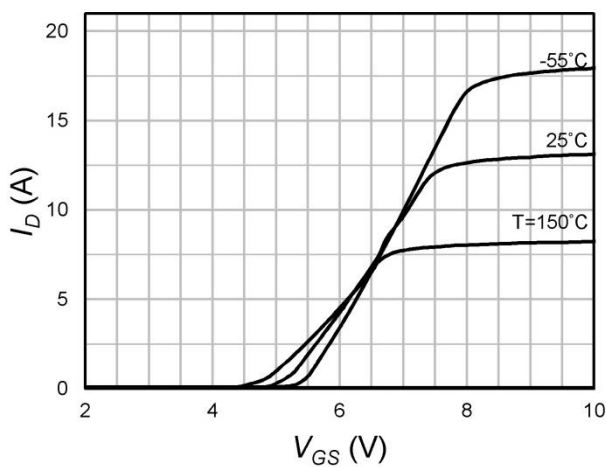
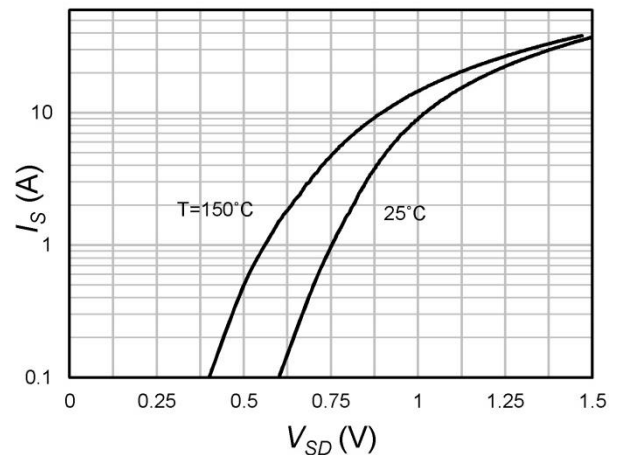
**■ Dynamic Characteristics ( $T_c=25^\circ\text{C}$  unless otherwise specified)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Input Capacitance	$C_{iss}$	-	575	-	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Output Capacitance	$C_{oss}$	-	430	-		
Reverse Transfer Capacitance	$C_{rss}$	-	20	-		
Effective Output Capacitance Energy Related <sup>(3)</sup>	$C_{o(er)}$	-	16	-		$V_{DS} = 0V \text{ to } 480V, V_{GS} = 0V, f = 1.0MHz$
Turn On Delay Time	$t_{d(on)}$	-	11	-	ns	$V_{GS} = 10V, R_G = 25\Omega, V_{DS} = 300V, I_D = 5.7A$
Rise Time	$t_r$	-	31	-		
Turn Off Delay Time	$t_{d(off)}$	-	37	-		
Fall Time	$t_f$	-	23	-		
Total Gate Charge	$Q_g$	-	15	-	nC	$V_{GS} = 10V, V_{DS} = 480V, I_D = 5.7A$
Gate – Source Charge	$Q_{gs}$	-	4.5	-		
Gate – Drain Charge	$Q_{gd}$	-	6	-		
Gate Resistance	$R_G$	-	4.5	-	$\Omega$	$V_{GS} = 0V, f = 1.0MHz$

3)  $C_{o(er)}$  is a capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0V to 80%  $V_{(BR)DSS}$

**■ Reverse Diode Characteristics ( $T_c=25^\circ\text{C}$  unless otherwise specified)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Continuous Diode Forward Current	$I_{SD}$	-	-	5.7	A	
Diode Forward Voltage	$V_{SD}$	-	-	1.4	V	$I_{SD} = 5.7\text{ A}$ , $V_{GS} = 0\text{ V}$
Reverse Recovery Time	$t_{rr}$	-	255	-	ns	$I_{SD} = 5.7\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$
Reverse Recovery Charge	$Q_{rr}$	-	1.7	-	$\mu\text{C}$	
Reverse Recovery Current	$I_{rrm}$	-	13.1	-	A	

**Fig.1 On-Region Characteristics.**

**Fig.2 On-Resistance Variation with Drain Current and Gate Voltage**

**Fig.3 On-Resistance Variation with Temperature (Normalized)**

**Fig.4 Breakdown Voltage Variation vs. Temperature (Normalized)**

**Fig.5 Transfer Characteristics**

**Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature**


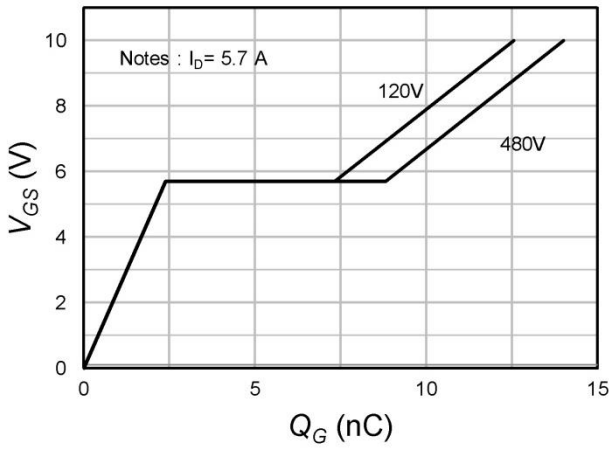
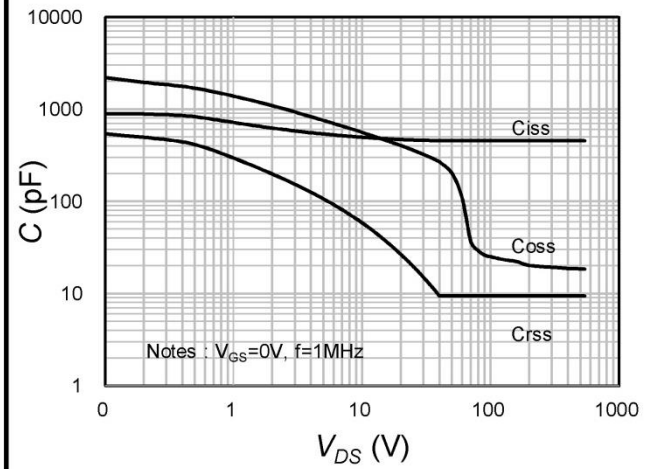
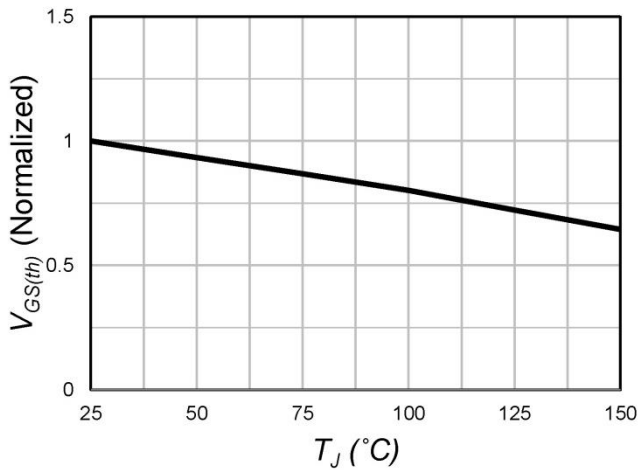
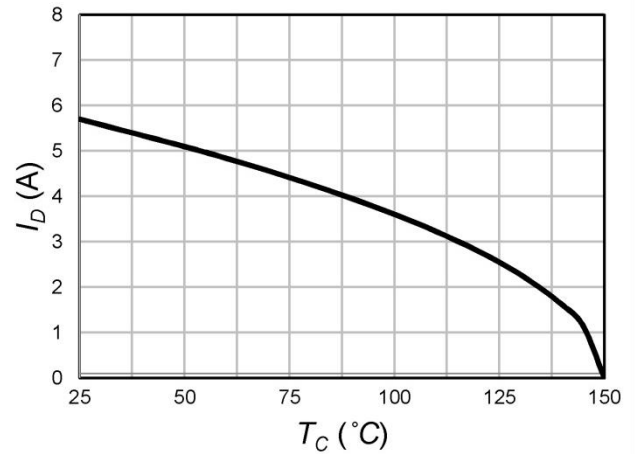
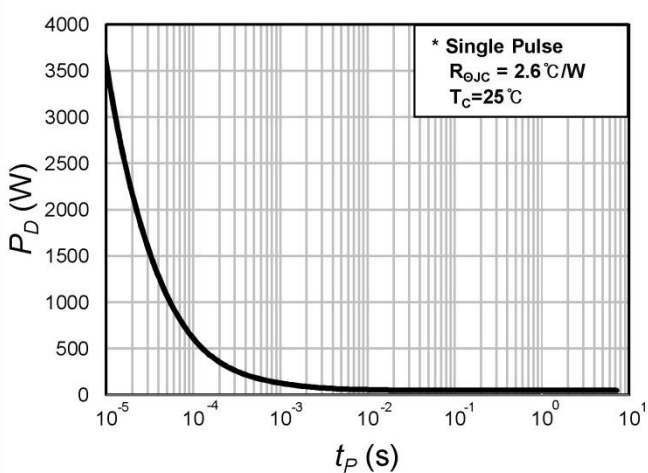
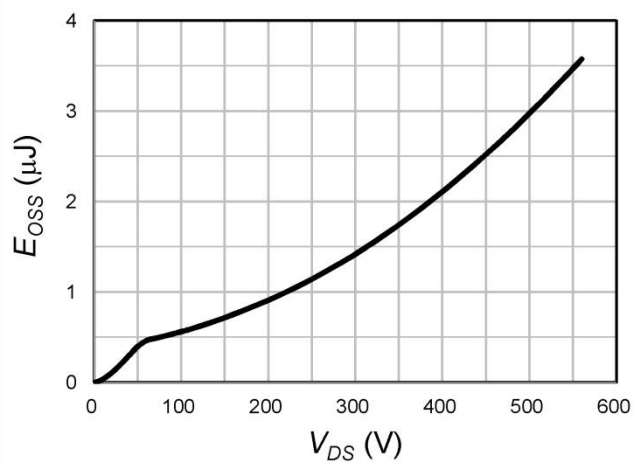
**Fig.7 Gate Charge Characteristics**

**Fig.8 Capacitance Characteristics**

**Fig.9  $V_{GS(th)}$  Variation with Temperature (Normalized)**

**Fig.10 Maximum Drain Current vs. Case Temperature**

**Fig.11 Single Pulse Maximum Power Dissipation**

**Fig.12 Output Capacitance Stored Energy**


Fig.13 Transient Thermal Response Curve

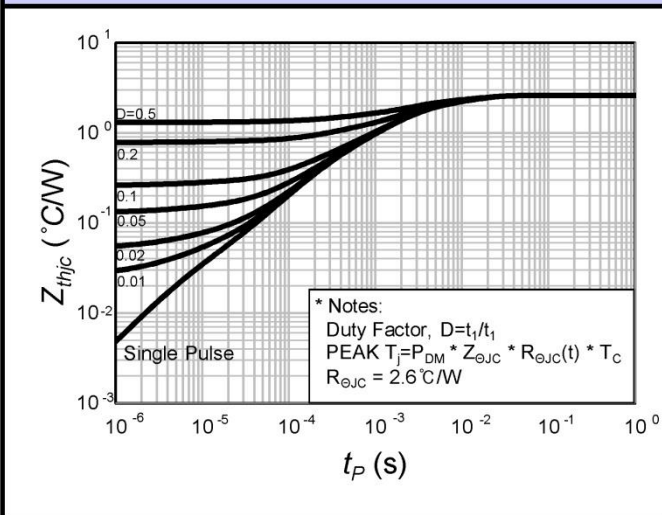
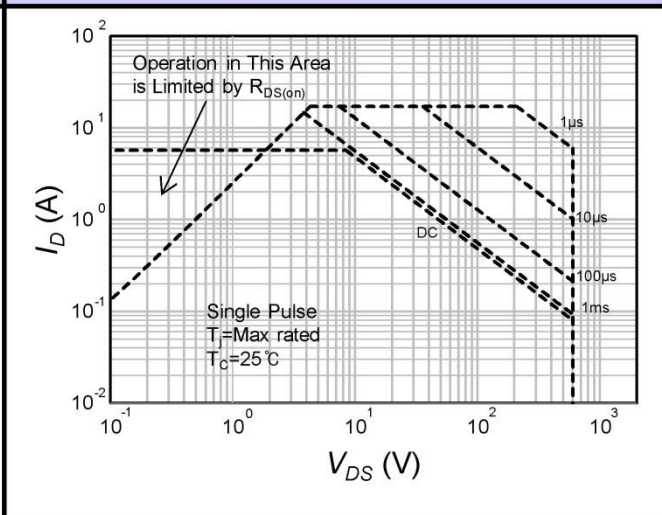
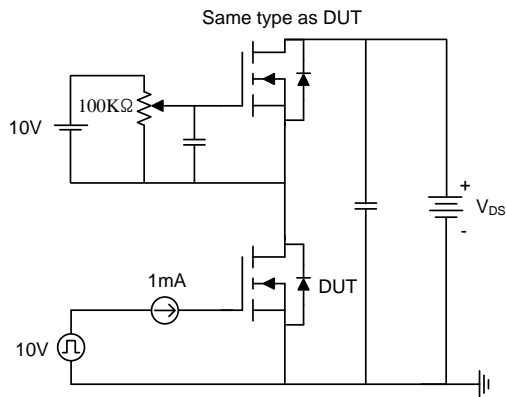
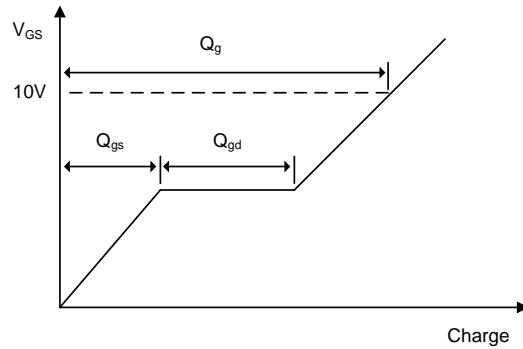
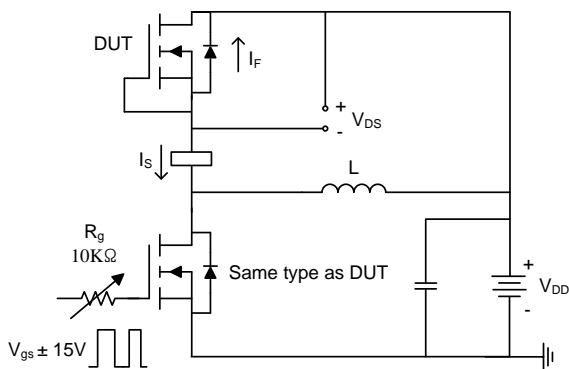
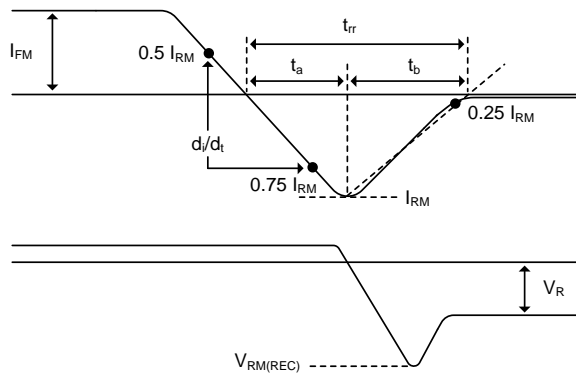
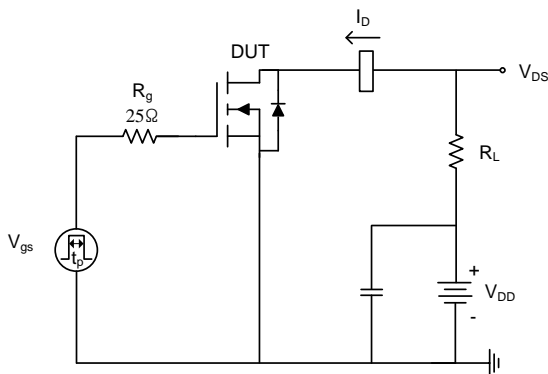
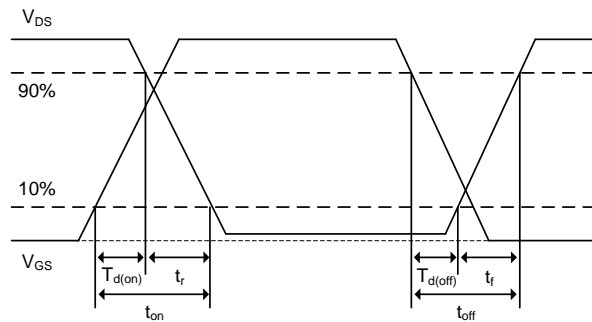
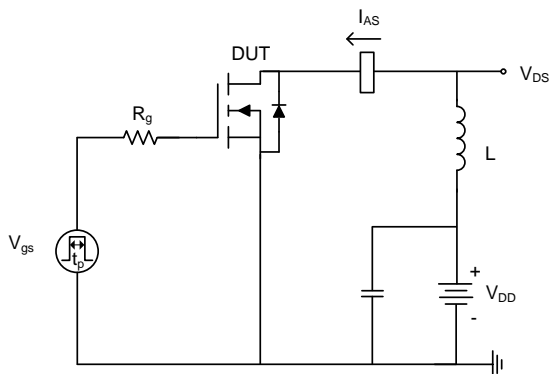
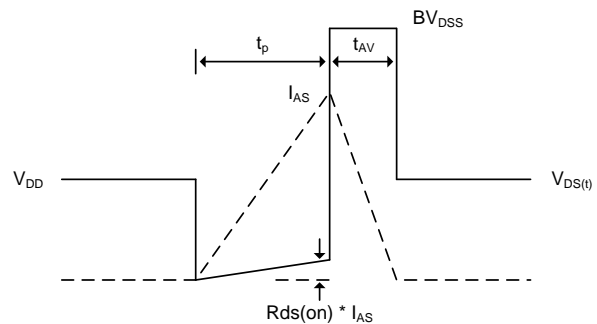
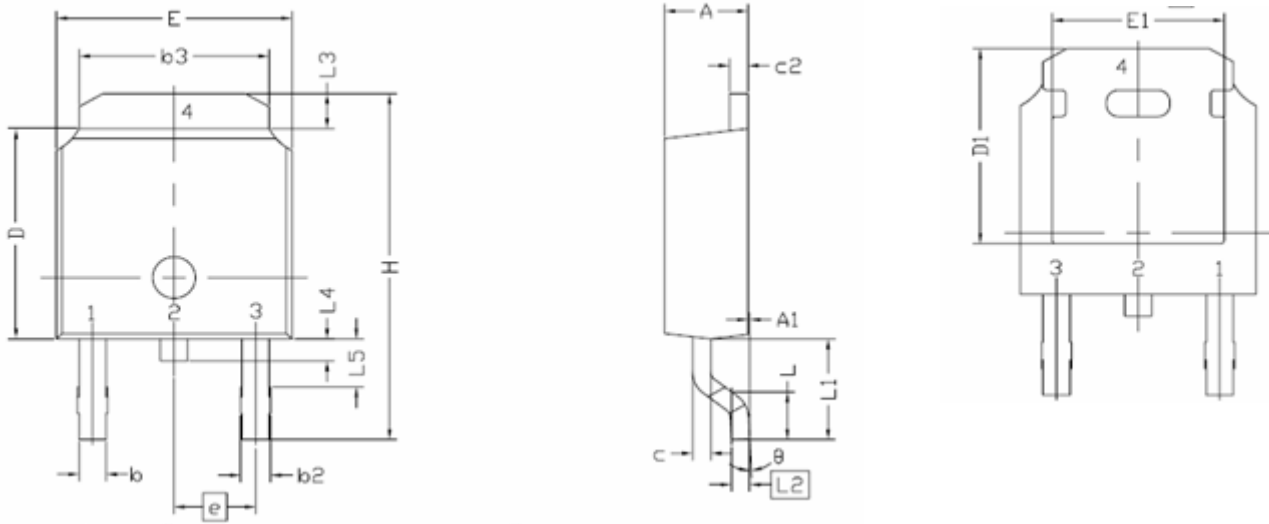


Fig.14 Maximum Safe Operating Area



**■ Test Circuit**

**Fig15-1. Gate charge measurement circuit**

**Fig15-2. Gate charge waveform**

**Fig16-1. Diode reverse recovery test circuit**

**Fig16-1. Diode reverse recovery test waveform**

**Fig17-1. Switching time test circuit for resistive load**

**Fig17-2. Switching time waveform**

**Fig18-1. Unclamped inductive load test circuit**

**Fig18-2. Unclamped inductive waveform**




**■ Physical Dimensions**
**TO-252 (2L)**
**Dimensions are in millimeters, unless otherwise specified**


Symbol	Min.	Nom.	Max.
E	6,35	-	6,73
L	1,40	1,52	1,78
L1	2,74 REF		
L2	0,508 BCS		
L3	0,89	-	1,27
L4	-	-	1,02
L5	1,14	-	1,52
D	5,97	6,10	6,22
H	9,40	-	10,41
b	0,64	-	0,89
b2	0,76	-	1,14
b3	4,95	-	5,46
e	2,286 BSC		
A	2,18	-	2,39
A1	-	-	0,13
c	0,46	-	0,61
c2	0,46	-	0,89
D1	5,21	-	-
E1	4,32	-	-
θ	0,00	-	10,00

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